COMPLIANT

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1200 V Gen 3 Power SiC Merged PIN Schottky Diode, 2 A



Cathode O Anode

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _F	2 A				
V _R	1200 V				
V _F at I _F at 25 °C, typ.	1.35 V				
T _J max.	175 °C				
I _R at V _R at 175 °C	5.0 μA				
Q _C (V _R = 800 V)	13 nC				
Package	SlimSMA HV (DO-221AC)				
Circuit configuration	Single				

FEATURES

- Minimum creepage distance 3.2 mm guaranteed by design
 RoHS
- Comparative Tracking Index: $CTI \ge 600$
- High CTI molding compound provides excellent electrical insulation at relevant working voltages
 FREE
- Positive V_F temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 $^{\circ}\mathrm{C}$
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 1200 V Schottky diode, designed for high performance and ruggedness.

Optimized for extreme high-speed hard switching over a wide temperature range. It is suited for demanding applications, such as bootstrap and anti-parallel diodes in AC/DC and DC/DC converters.

MECHANICAL DATA

Case: SlimSMA HV (DO-221AC)

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

MAXIMUM RATINGS (T _A = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		1200	V		
Continuous forward current	١ _F	T _M = 130 °C (DC) ⁽¹⁾	2	А		
DC blocking voltage	V _{DC}		1200	V		
Repetitive peak forward current	I _{FRM}	T_{M} = 25 °C, f = 50 Hz, square wave, DC = 25 $\%$	6.5			
Non-repetitive peak forward surge current	I _{FSM}	$T_M = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ half sine wave}$	21	А		
		T _M = 110 °C, t _p = 10 ms, half sine wave	18			
	P _{tot} ⁽¹⁾	T _M = 25 °C	12.5 W			
Dewer dissipation	Ftot ("	T _M = 110 °C	5.4	vv		
Power dissipation	P _{tot} ⁽²⁾	T _M = 25 °C	9.7	w		
	Ptot (2)	T _M = 110 °C	4.2	- vv		
124	∫i ² dt	T _M = 25 °C	2.2	A2-		
l ² t value		T _M = 110 °C	1.6	A ² s		
Operating junction and storage temperatures	T _J ⁽³⁾ , T _{Stg}		-55 to +175	°C		

Notes

(1) Based on typical Rth

⁽²⁾ Based on maximum R_{th}

⁽³⁾ The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta JA}$

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ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
		I _F = 2 A	-	1.35	1.50		
Forward voltage	V _F	I _F = 2 A, T _J = 150 °C	-	1.73	2.00	V	
		I _F = 2 A, T _J = 175 °C	-	1.85	-		
		V _R = V _R rated	-	0.15	15		
Reverse leakage current	I _R	$V_R = V_R$ rated, $T_J = 150 \ ^\circ C$	-	0.85	30	μA	
		$V_R = V_R$ rated, $T_J = 175 \ ^\circ C$	-	5.0	-		
Total capacitance	С	V _R = 1 V, f = 1 MHz	-	125	-	pF	
	U	V _R = 800 V, f = 1 MHz	-	9.5	-		
Total capacitive charge	Q _C	V _R = 800 V, f = 1 MHz	-	13	-	nC	

THERMAL AND MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to mount	R _{thJM} ⁽¹⁾		-	12	15.5	°C/W
Marking device				C2	212	

Note

⁽¹⁾ Thermal resistance junction-to-mount follows JEDEC[®] 51-14 transient dual interface test method (TDIM)

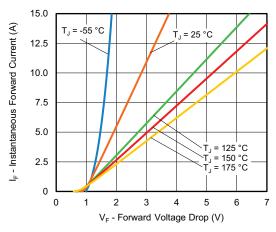
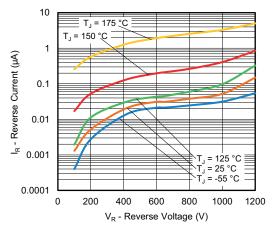


Fig. 1 - Typical Forward Voltage Drop Characteristics





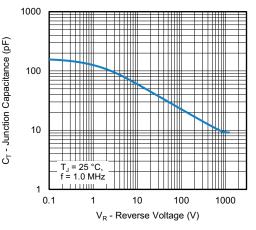
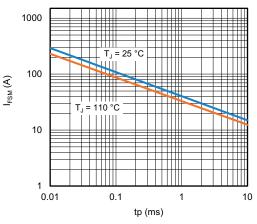
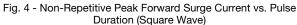


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



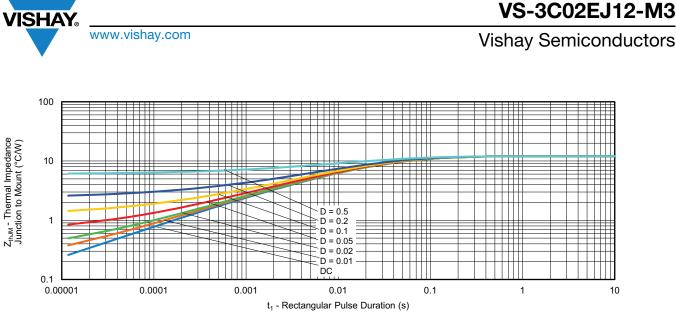


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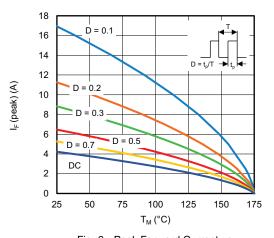


Fig. 6 - Peak Forward Current vs. Maximum Allowable Mount Temperature

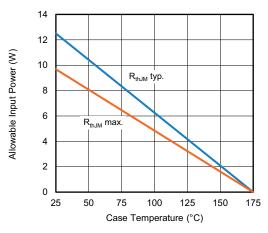


Fig. 7 - Forward Power Loss Characteristics

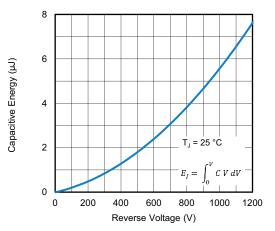


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

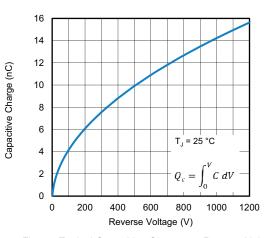


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

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ORDERING INFORMATION TABLE

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Device code	VS-	3C	02	Е	J	12	-M3	
		2	3	4	5	6	7	
	1	- Vis	hay Sen	nicondu	ctors pro	oduct		
	2	- 3C	= SiC c	diode, ge	eneratio	n 3		
	3	- Cui	Current rating $(02 = 2 \text{ A})$					
	4	- E=	E = single diode					
	5	- J=	J = SlimSMA HV package					
	6	- Vol	tage rati	ing: (12	= 1200 '	V)		
	7	- Env	vironmer	ntal digit	t:			
		-M	3 = halo	gen-free	e, RoHS	-complia	ant, and	

ORDERING INFORMATION						
PREFERRED P/N	UNIT WEIGHT (g)	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-3C02EJ12-M3/H	0.032	3500 per reel	7" diameter plastic tape and reel			
VS-3C02EJ12-M3/I	0.032	14 000 per reel	13" diameter plastic tape and reel			

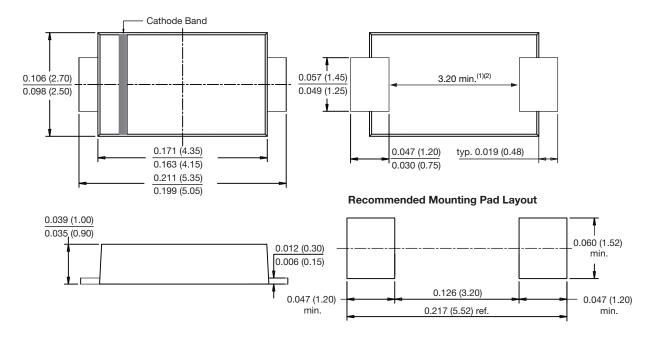
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?97278				
Part marking information	www.vishay.com/doc?98699				
Packaging information	www.vishay.com/doc?98714				



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SlimSMA HV (DO-221AC)

DIMENSIONS in inches (millimeters)



Notes

- ⁽¹⁾ Minimum creepage distance is defined and guaranteed by design
- ⁽²⁾ For high voltage applications, end users should consider the relevant guidelines and normative on creepage and clearance distances between device terminals and PCB pads.



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